

## United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/705,891	11/13/2003	Yun-Ho Jung	053785-5160	6104	
30827 75	90 07/28/2006	EXAMINER			
MCKENNA LONG & ALDRIDGE LLP 1900 K STREET, NW			ROSASCO, STEPHEN D		
WASHINGTON		ART UNIT	PAPER NUMBER		
	•		1756	1756	
			DATE MAILED: 07/28/2006		

Please find below and/or attached an Office communication concerning this application or proceeding.

-		Applicat	on No	Applicant(s)			
Office Action Summary					•		
		10/705,8	91	JUNG, YUN-HO			
		Examine	r	Art Unit			
		Stephen		1756			
Period fo	The MAILING DATE of this communications Reply	n appears on th	e cover sheet with the c	orrespondence ad	dress		
WHIC - Exter after - If NO - Failu Any	ORTENED STATUTORY PERIOD FOR RECHEVER IS LONGER, FROM THE MAILIN nsions of time may be available under the provisions of 37 C SIX (6) MONTHS from the mailing date of this communication period for reply is specified above, the maximum statutory reto reply within the set or extended period for reply will, by reply received by the Office later than three months after the end patent term adjustment. See 37 CFR 1.704(b).	NG DATE OF TO CFR 1.136(a). In no exon. period will apply and verstatute, cause the ap	HIS COMMUNICATION  vent, however, may a reply be tin  viil expire SIX (6) MONTHS from  polication to become ABANDONE	N. nely filed the mailing date of this of 0 (35 U.S.C. § 133).			
Status							
2a)□	Responsive to communication(s) filed on This action is <b>FINAL</b> . 2b) Since this application is in condition for all closed in accordance with the practice un	This action is a	t for formal matters, pro		e merits is		
Dienositi	on of Claims						
5)□ 6)⊠ 7)□ 8)□	Claim(s) <u>1-25</u> is/are pending in the applic 4a) Of the above claim(s) <u>23-25</u> is/are with Claim(s) is/are allowed. Claim(s) <u>1-22</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction a	hdrawn from co					
Applicati	on Papers						
10)	The specification is objected to by the Exa The drawing(s) filed on is/are: a) Applicant may not request that any objection t Replacement drawing sheet(s) including the c The oath or declaration is objected to by the	accepted or b to the drawing(s) correction is requi	be held in abeyance. See red if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CF			
Priority ι	ınder 35 U.S.C. § 119	•					
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  a) All b) Some * c) None of:  1. Certified copies of the priority documents have been received.  2. Certified copies of the priority documents have been received in Application No  3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  * See the attached detailed Office action for a list of the certified copies not received.							
2)  Notic 3) Infor	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-94 nation Disclosure Statement(s) (PTO-1449 or PTO/S		4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P	ate	D-152)		
Pape	r No(s)/Mail Date		6) 🗌 Other:				

## **Detailed Action**

In response to the Amendment of 5/2/06, wherein the claims were amended to include the limitation that the reflecting layer "has a refractive index and a thickness such that the reflective layer" totally reflects the laser beam, the examiner withdraws the prior office action rejections and includes new rejections here.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 3-4 and 12, 14 are rejected under 35 U.S.C. 102(b) as being clearly anticipated by Iwamatsu et al. (5,609,977).

Iwamatsu et al. teach a reflection phase shifting mask comprising: a substrate for reflecting exposure light, and a phase shifting layer, wherein the thickness and refractive index of said phase shifting layer are set such that light reflected by said phase shifting layer has substantially the same phase as that of light which is transmitted through said phase shifting layer, reflected by said substrate, and output from said phase shifting layer.

Iwamatsu et al. also teach that the mask blank is to be used together with a KrF laser beam as exposure light can also be manufactured by the same method except that the composition ratio of oxygen is changed.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Doany et al. (5,387,484) in view of Iwamatsu (5,609,977).

The claimed invention is directed to a laser beam mask for shaping a laser beam, comprising: a base substrate having first and second surfaces; and a reflecting layer on the first surface of the base substrate, wherein the reflecting layer has a refractive index and a thickness such that the reflective layer totally reflects the laser beam.

And wherein the laser beam is transmitted from the base substrate to the reflecting layer.

Doany et al. teach a mask and a fabrication method therefor that incorporates a patterned radiation blocking layer such as a second patterned high-reflectivity dielectric coating on the back surface of the mask which also includes a first patterned reflective coating on the front. This second high-reflective dielectric coating referred to as a premask, eliminates most of the laser energy directed onto the mask that leads only to substrate heating without effecting the laser energy transmitted through the open area of the mask.

Iwamatsu et al. teach a reflection phase shifting mask comprising: a substrate for reflecting exposure light, and a phase shifting layer, wherein the thickness and refractive index of said phase shifting layer are set such that light reflected by said phase shifting layer has substantially the same phase as that of light which is transmitted through said phase shifting layer, reflected by said substrate, and output from said phase shifting layer.

The teachings of Doany et al. differ from those of the applicant in that the applicant teaches adjusting the refractive index and thickness such that the reflecting layer totally reflects the laser beam.

Iwamatsu is included here as discussed above.

It would have been obvious to one having ordinary skill in the art to take the teachings of Doany et al. and combine them with the teachings of Iwamatsu in order to make the claimed invention because it would be obvious to make the reflecting layer totally reflecting based on the teachings of Iwamatsu for adjusting the index of refraction and thickness to give the desired result.

Applicant's arguments with respect to claims 1-22 have been considered but are most in view of the new ground(s) of rejection.

## Conclusion

Any inquiry concerning this communication or earlier communications from the Examiner should be directed to Stephen Rosasco whose telephone number is (571) 272-1389. The Examiner can normally be reached Monday-Friday, from 8:00 AM to 4:30 PM. The Examiner's supervisor, Mark Huff, can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

S. Rosasco

Primary Examiner

Art Unit 1756

S.Rosasco 7/18/06